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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HC323

8-bit Universal Shift/Storage Register (with 3-state Outputs)

ADE-205-489 (Z)
1st. Edition
Sep. 2000

Description

This eight-bit universal register features multiplexed I/O ports to achieve full eight bit data handling in a single 20-pin package. HD74HC323 applications are as stacked or push-down registers, buffer storage, and accumulator registers.

Two function-select inputs and two output control inputs can be used to choose the modes of operation listed in the function table.

Synchronous parallel loading is accomplished by taking both function-select lines S_0 and S_1 high. This places the three-state outputs in a high-impedance state, which permits data that is applied on the I/O ports to be clocked into the register. Reading out of this register can be accomplished while the outputs are enabled in any mode. The clear function is synchronous, and a low level at the clear input clears the register on the next low-to-high transition of the clock.

Features

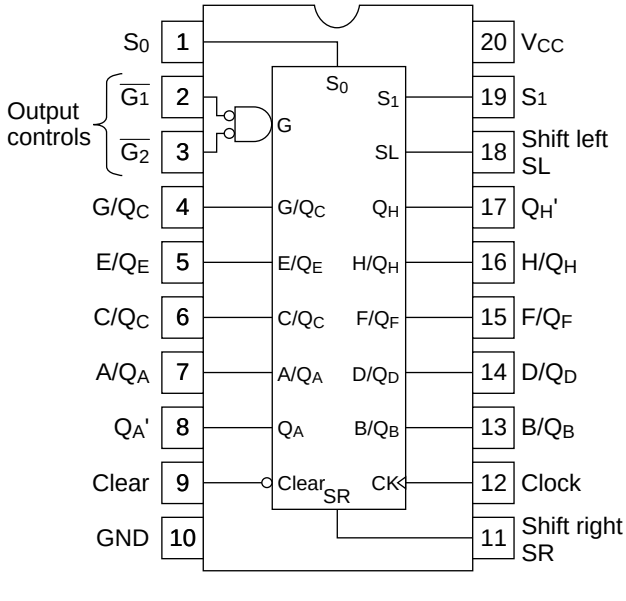
- High Speed Operation: t_{pd} (Clock to Q) = 20 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 2 to 6 V
- Low Input Current: 1 μA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μA max (Ta = 25°C)

Function Table

	Inputs																	
		Function Select		Output Control			Serial		Inputs/Outputs								Outputs	
Mode	Clear	S_1	S_0	$\overline{G}_1$†	$\overline{G}_2$†	Clock	S_L	S_R	A/Q_A	B/Q_B	C/Q_C	D/Q_D	E/Q_E	F/Q_F	G/Q_G	H/Q_H	Q_A'	Q_H'
Clear	L	X	L	L	L	↑	X	X	L	L	L	L	L	L	L	L	L	L
	L	L	X	L	L	↑	X	X	L	L	L	L	L	L	L	L	L	L
Hold	H	L	L	L	L	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}	Q_{E0}	Q_{F0}	Q_{G0}	Q_{H0}	Q_{A0}	Q_{H0}
	H	X	X	L	L	L	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}	Q_{E0}	Q_{F0}	Q_{G0}	Q_{H0}	Q_{A0}	Q_{H0}
Shift	H	L	H	L	L	↑	X	H	H	Q_{An}	Q_{Bn}	Q_{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	H	Q_{Gn}
Right	H	L	H	L	L	↑	X	L	L	Q_{An}	Q_{Bn}	Q_{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	L	Q_{Gn}
Shift	H	H	L	L	L	↑	H	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	Q_{Hn}	H	Q_{Bn}	H
Left	H	H	L	L	L	↑	L	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	Q_{En}	Q_{Fn}	Q_{Gn}	Q_{Hn}	L	Q_{Bn}	L
Load	H	H	H	X	X	↑	X	X	a	b	c	d	e	f	g	h	a	h

a ... h = the level of the steady-state input at A through H, respectively. These data are loaded into the flip-flops while the flip-flop outputs are isolated from the input/output terminals.

Pin Arrangement

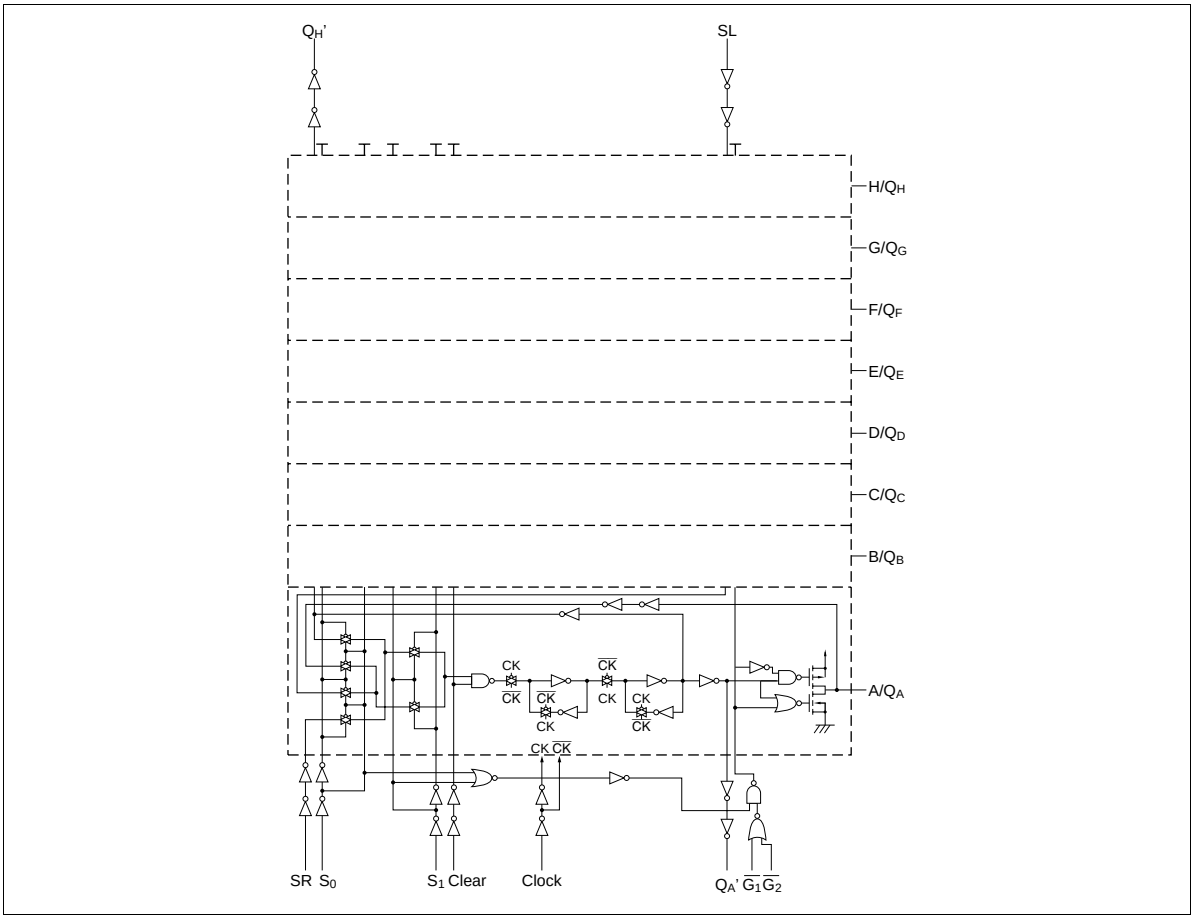


(Top view)

Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
Output current	I_{OUT}	±35	mA
DC current drain per V_{CC}, GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

Logic Diagram



DC Characteristics

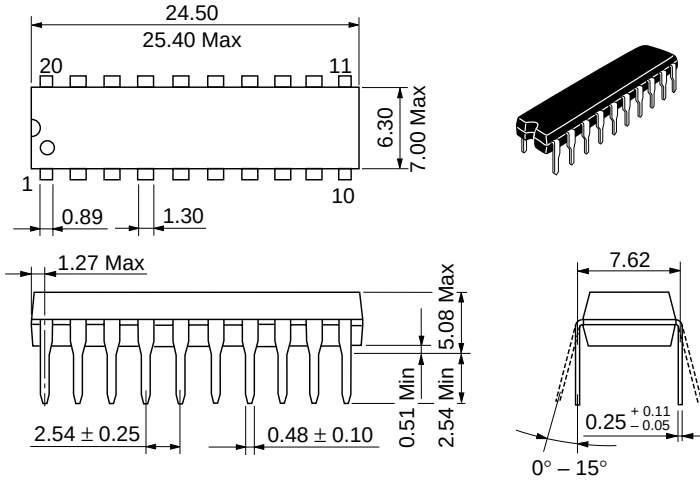
Item	Symbol	V_{CC} (V)	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions	
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V_{IH} or V_{IL}	I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—		Q_A to Q_H	I_{OH} = –6 mA
		6.0	5.68	—	—	5.63	—			I_{OH} = –7.8 mA
		4.5	4.18	—	—	4.13	—		Q_A', Q_H'	I_{OH} = –4 mA
		6.0	5.68	—	—	5.63	—			I_{OH} = –5.2 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V_{IH} or V_{IL}	I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33		Q_A to Q_H	I_{OH} = 6 mA
		6.0	—	—	0.26	—	0.33			I_{OH} = 7.8 mA
		4.5	—	—	0.26	—	0.33		Q_A', Q_H'	I_{OH} = 4 mA
		6.0	—	—	0.26	—	0.33			I_{OH} = 5.2 mA
Off-state output current	I_{OZ}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND	
Input current	Iin	6.0	—	—	±0.1	—	±1.0	µA	Vin = V_{CC} or GND	
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	µA	Vin = V_{CC} or GND, Iout = 0 µA	

AC Characteristics (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Maximum clock frequency	f_{max}	2.0	—	—	5	—	4	MHz	
		4.5	—	—	27	—	21		
		6.0	—	—	31	—	24		
Propagation delay time	t_{PLH} t_{PHL}	2.0	—	—	150	—	190	ns	Clock to Q_A' or Q_H'
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	33		
		2.0	—	—	175	—	220	ns	Clock to Q
		4.5	—	20	35	—	44		
		6.0	—	—	30	—	37		
Output enable time	t_{ZH} t_{ZL}	2.0	—	—	150	—	190	ns	
		4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{HZ} t_{LZ}	2.0	—	—	150	—	190	ns	
		4.5	—	15	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH} t_{THL}	2.0	—	—	75	—	95	ns	Q_A', Q_H'
		4.5	—	5	15	—	19		
		6.0	—	—	13	—	16		
		2.0	—	—	60	—	75	ns	Q
		4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	Cin	—	—	5	10	—	10	pF	

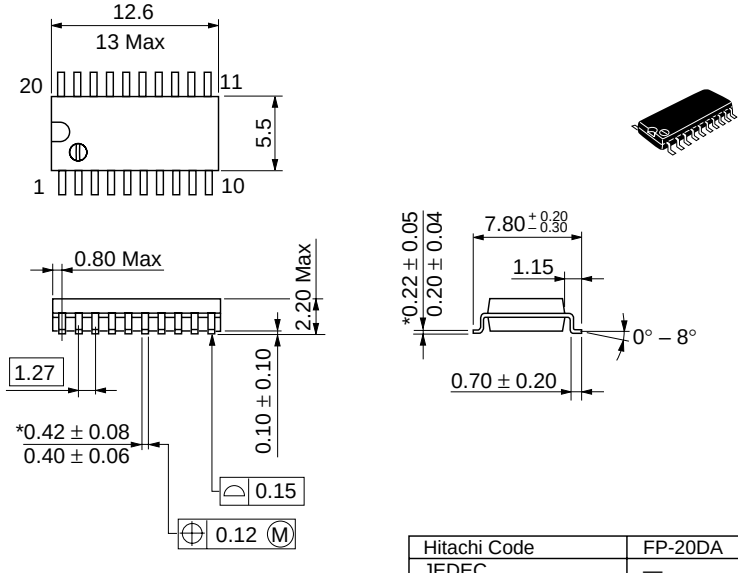
Package Dimensions

Unit: mm



Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.26 g

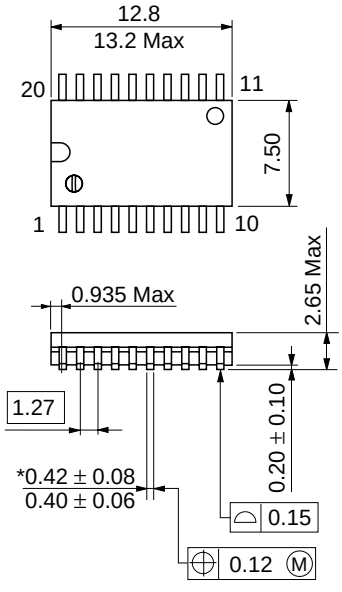
Unit: mm

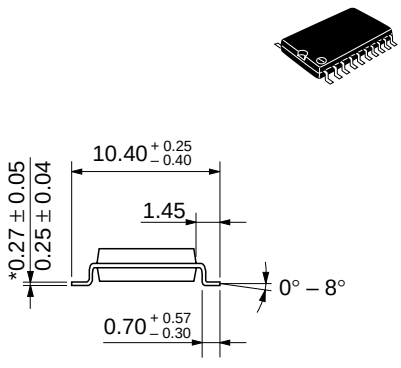


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.31 g

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.52 g

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